THE DATASHEET OF

ESD8V0R1B02ELSE6327XTSA1

TVS Diodes

Transient Voltage Suppressor Diodes

ESD8V0R1B Series

Bi-directional Low Capacitance TVS Diode

ESD8V0R1B-02EL
ESD8V0R1B-02ELS

Data Sheet

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Revision History	
Page or Item	**Subjects (major changes since previous revision)**
Revision 1.0, 2010-10-20	
Revision 2.0, 2010-12-15	
	Carrier Tape drawing for TSSLP-2-2 Package updated

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1 Bi-directional Low Capacitance TVS Diode

1.1 Features

- ESD / Transient protection of data lines in 3.3 / 5 / 12 V applications according to :
  - IEC61000-4-2 (ESD) : ±20 kV (air) and ±18 kV (contact)
  - IEC61000-4-4 (EFT) : 40 A (5/50ns)
- Extremely small form factor down to 0.62 x 0.32 x 0.31 mm²
- Maximum working voltage: V_{RWM} = -8 / +14 V
- Very low reverse current: I_R < 1 nA (typical)
- Very low series inducttance down to : L_S = 0.2 nH (typical)
- Low capacitance C_L = 4 pF I/O to GND (typical)
- Pb-free and Halogen-Free package (RoHS compliant)

1.2 Application Examples

- Keypad, touchpad, buttons, convenience keys
- LCD displays, Camera, audio lines, mobile communication, Consumer products (E-Book, MP3, DVD, DSC, ...)
- Notebooks tablets and desktop computers and their peripherals

2 Product Description

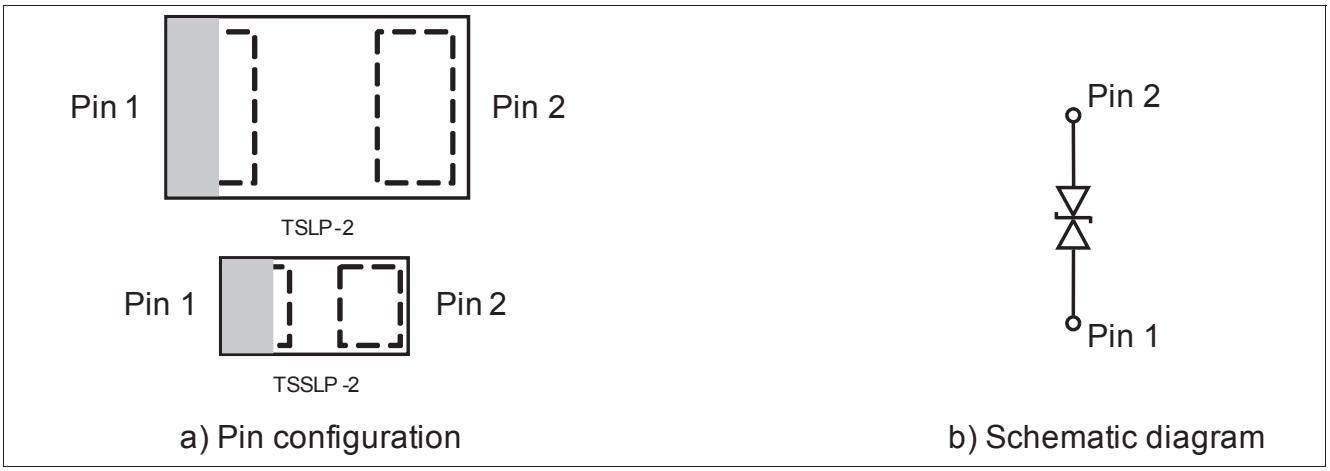


Figure 1 a) Pin Configuration and b) Schematic Diagram

Table 1 Ordering information

Type	Package	Configuration	Marking code
ESD8V0R1B-02EL	PG-TSLP-2-18	1 line, bi-directional	R
ESD8V0R1B-02ELS	PG-TSSLP-2-2	1 line, bi-directional	D

3 Characteristics

Table 2 Maximum Rating at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
ESD air discharge[1]	V_{ESD}	-20	–	20	kV
ESD contact discharge[1]	V_{ESD}	-18	–	18	kV
Peak pulse current (t_p = 8/20 µs)[2]	I_{PP}	-1	–	1	A
Operating temperature	T_{OP}	-55	–	150	°C
Storage temperage	T_{stg}	-65	–	150	°C

1) V_{ESD} according to IEC61000-4-2

2) I_{PP} according to IEC61000-4-5

3.1 Electrical Characteristics at T_A = 25 °C, unless otherwise specified

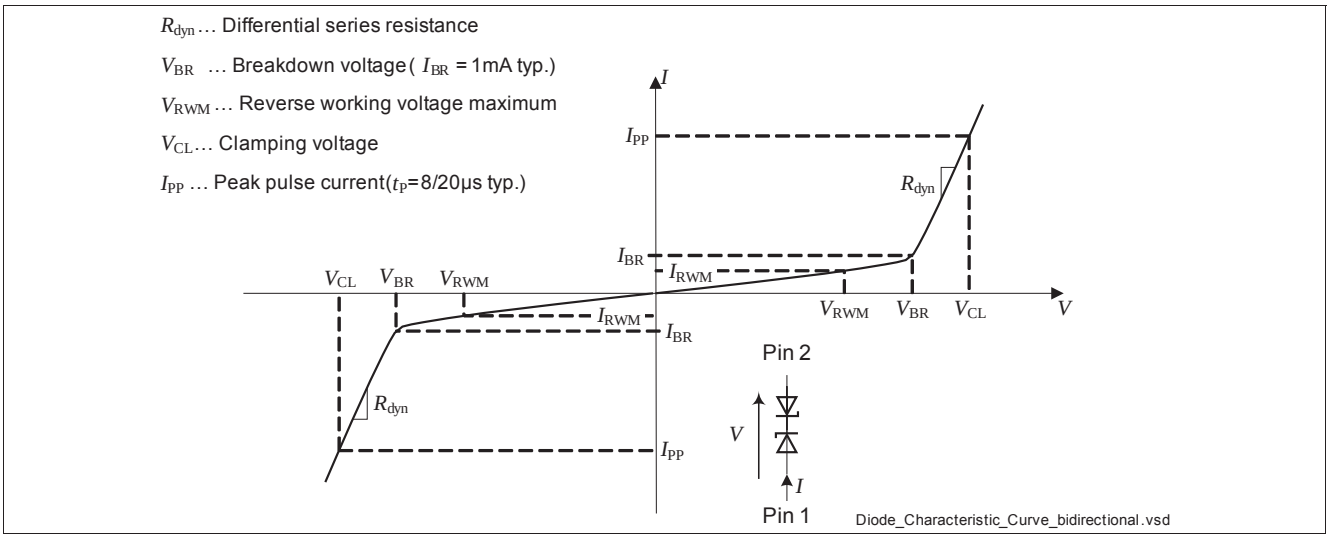


Figure 2 Definitions of electrical characteristics

Table 3 DC characteristics at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Reverse working voltage	V_{RWM}	-8	–	14	V	from Pin2 to Pin1
Breakdown voltage	V_{BR}	8.5	11	14	V	I_R = 1 mA, from Pin1 to Pin2
Breakdown voltage	V_{BR}	14.5	17	20	V	I_R = 1 mA, from Pin2 to Pin1
Reverse current	I_R	–	<1	50	nA	V_R = 3.3 V

Table 4 RF characteristics at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Line capacitance	C_L	–	4	7	pF	V_R = 0 V, f = 1 MHz, I/O to GND
Serie inductance	L_S	–	0.4	–	nH	ESD8V0R1B-02EL
	L_S	–	0.2	–	nH	ESD8V0R1B-02ELS

Table 5 ESD characteristics at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Clamping voltage[1)]	V_{CL}	–	17	22	V	I_{PP} = 1 A from Pin1 to Pin2
	V_{CL}	–	23	28	V	I_{PP} = 1 A from Pin2 to Pin1

1) According to IEC61000-4-5 (t_p : 8 / 20 µs)

3.2 Typical Performance characteristics at T_A = 25 °C, unless otherwise specified

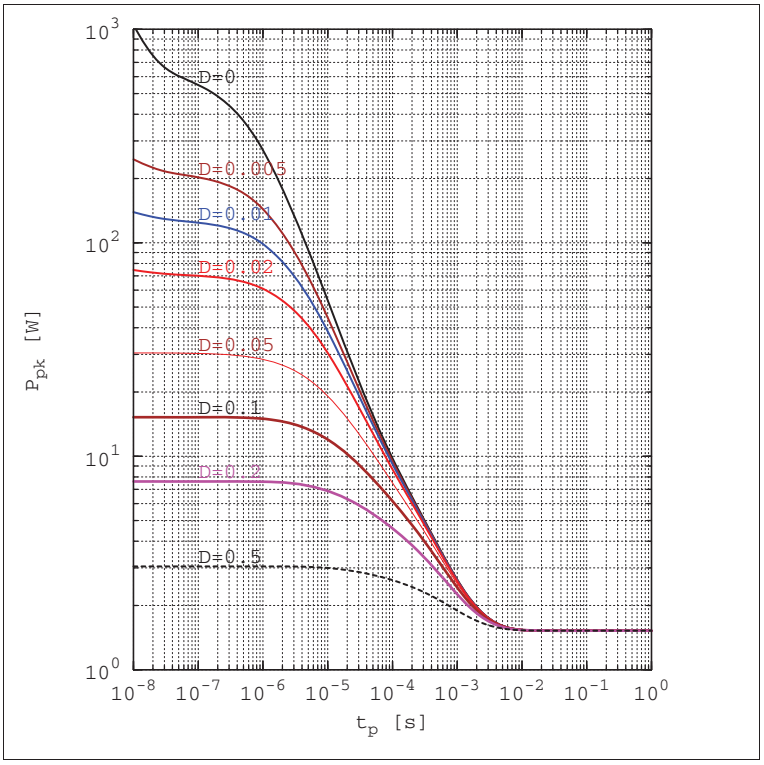


Figure 3 Non-repetitive peak pulse power: $P_{pk} = f(t_p)$

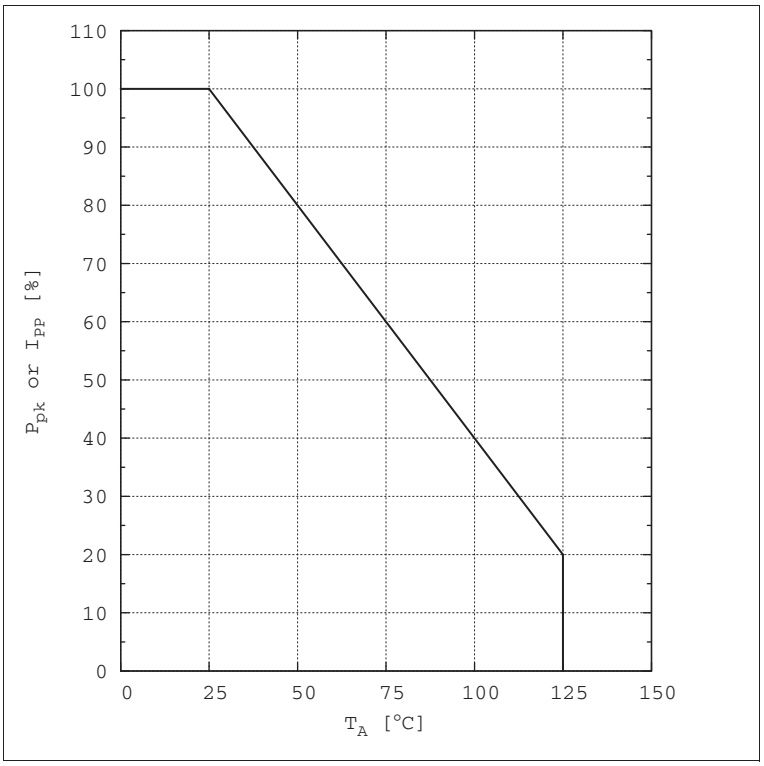


Figure 4 Power derating curve: $P_{pk} = f(T_A)$

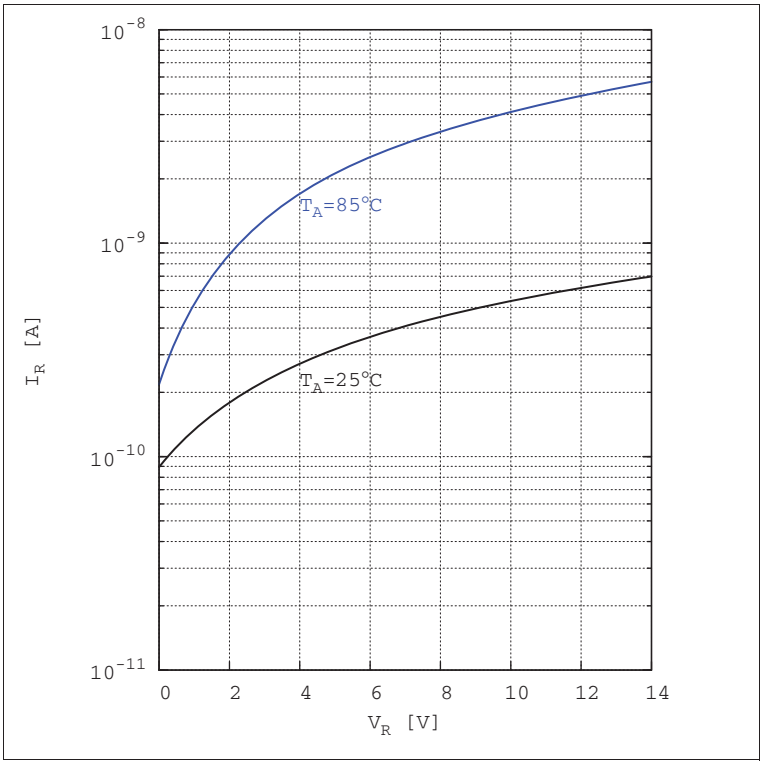


Figure 5 Reverse characteristic, $I_R = (V_R)$, T_A = parameter

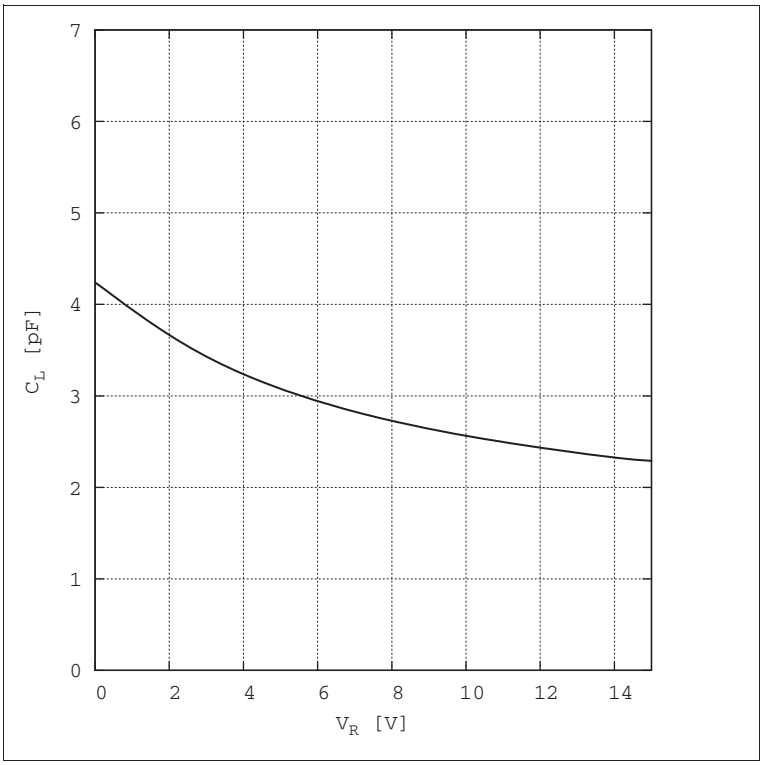


Figure 6 Line capacitance $C_L = f(V_R)$

4 Application Information

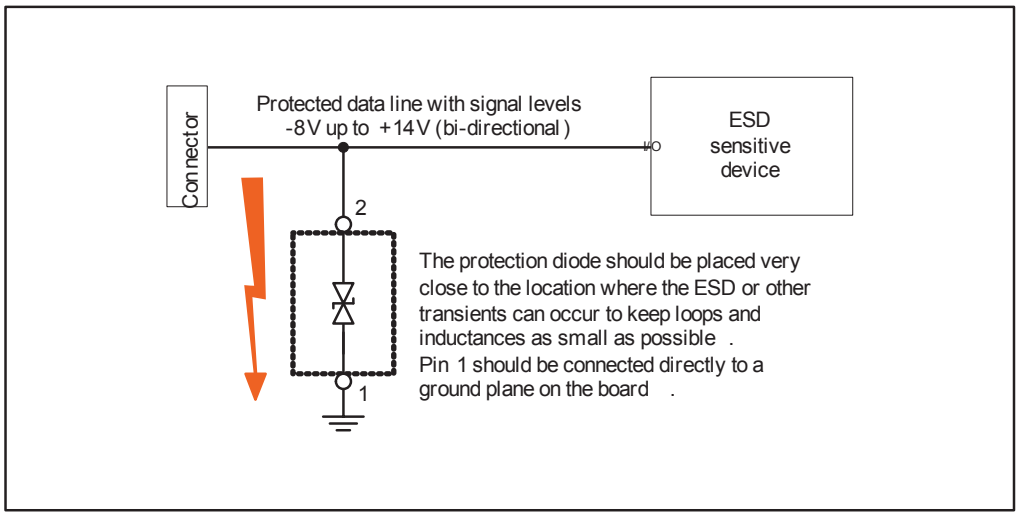


Figure 7 1 Line, bi-directional protection with ESD diode

5 Ordering information scheme

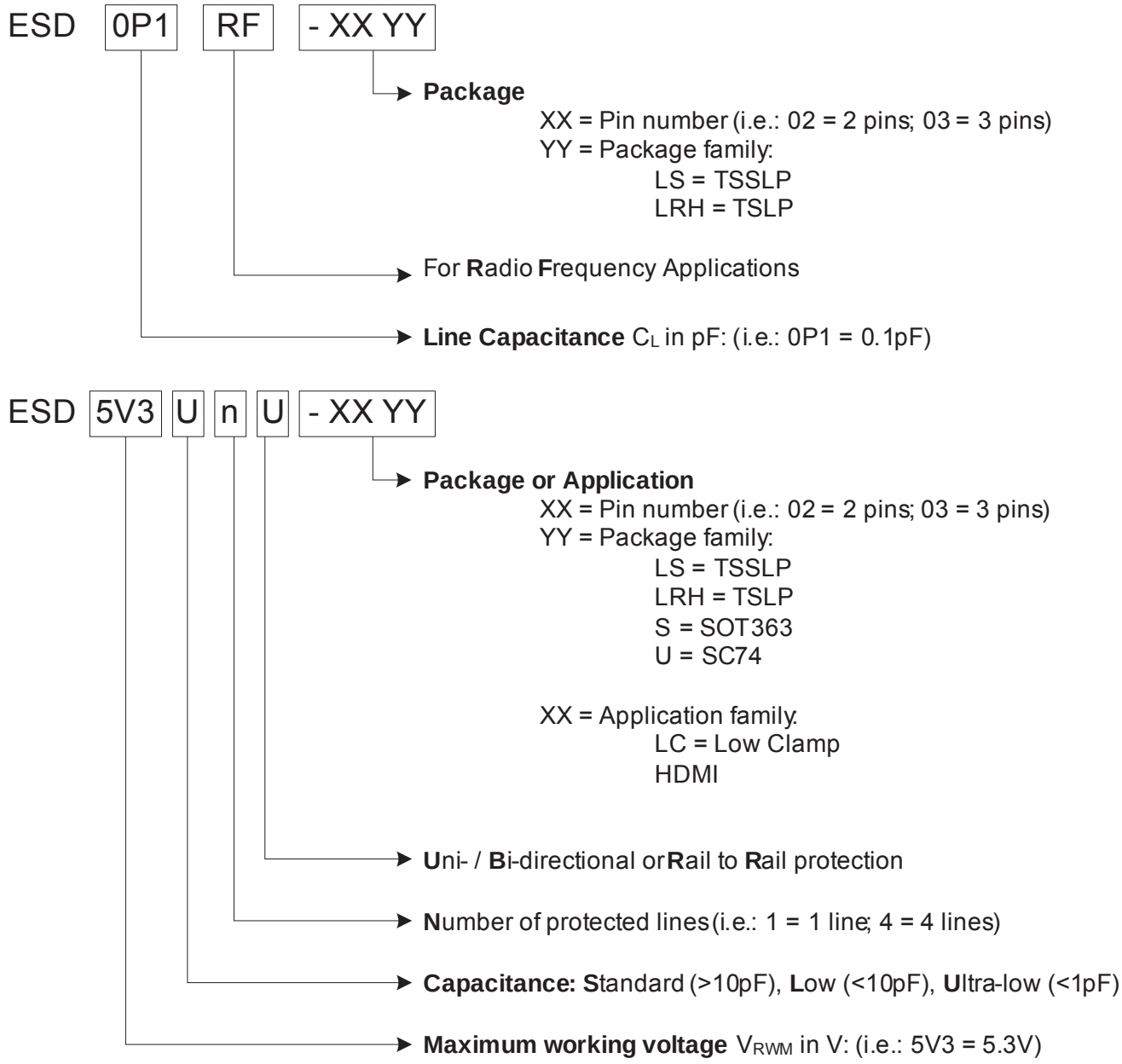


Figure 8 Ordering Information Scheme (examples)

6 Package Information

6.1 PG-TSLP-2-18

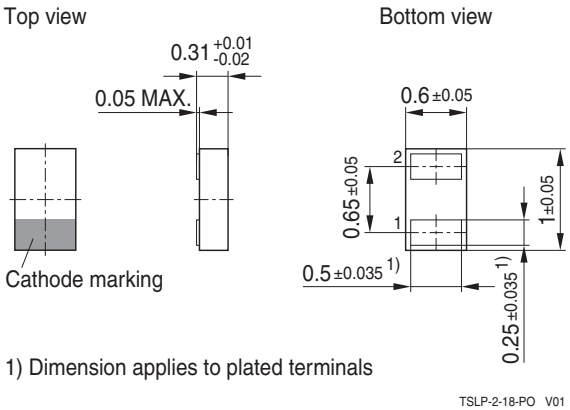


Figure 9 PG-TSLP-2-18: Package Overview

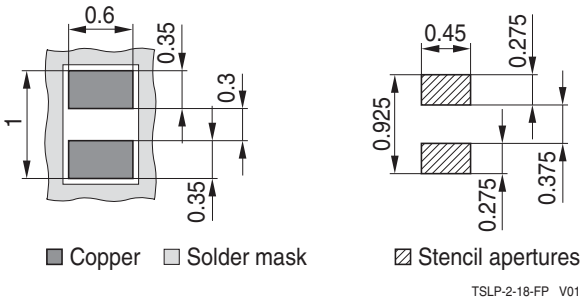


Figure 10 PG-TSLP-2-18: Footprint

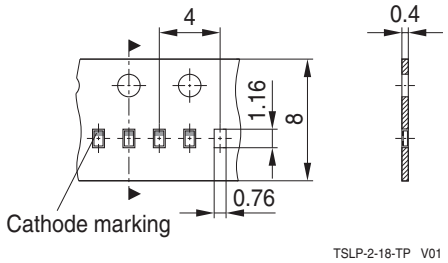


Figure 11 PG-TSLP-2-18: Packing

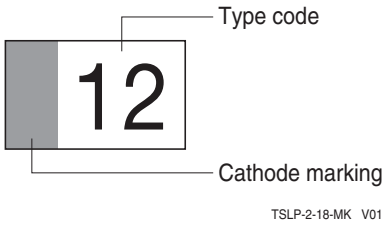


Figure 12 PG-TSLP-2-18: Marking (example)

6.2 PG-TSSLP-2-2

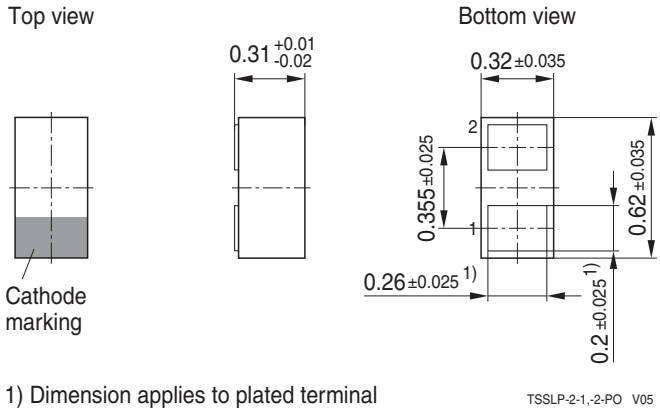


Figure 13 PG-TSSLP-2-2: Package Overview

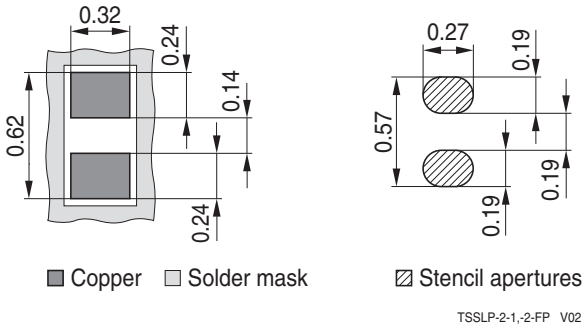
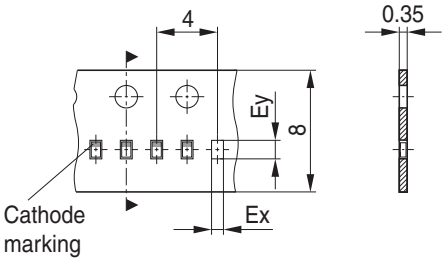


Figure 14 PG-TSSLP-2-2: Footprint



Tape type	Ex	Ey
Punched Tape	0.43	0.73
Embossed Tape	0.37	0.67

Deliveries can be both tape types (no selection possible).
Specification allows identical processing (pick & place) by users.

TSSLP-2-1,-2-TP V03

Figure 15 PG-TSSLP-2-2: Packing

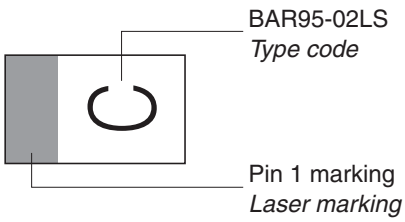


Figure 16 PG-TSSLP-2-2: Marking (example)

Terminology

C_L	Line capacitance
DSC	Digital Still Camera
DVD	Digital Versatile Disc
EFT	Electrical Fast Transient
ESD	Electrostatic Discharge
IEC	International Electrotechnical Commission
I_{PP}	Peak pulse current
I_R	Reverse current
I_{RWM}	Reverse working current maximum
LCD	Liquid Crystal Display
L_S	Serial inductance
MP3	Moving Picture Experts Group III
RoHS	Restriction of Hazardous Substances Directive
T_A	Ambient temperature
T_{OP}	Operation temperature
t_p	Pulse duration
T_{stg}	Storage temperature
V_{CL}	Reverse clamping voltage
V_{ESD}	Electrostatic discharge voltage
V_R	Reverse voltage
V_{RWM}	Reverse working voltage maximum

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